

n-channel JFET designed for . . .



**Performance Curves NRL/
NPA/NH See Section 4**

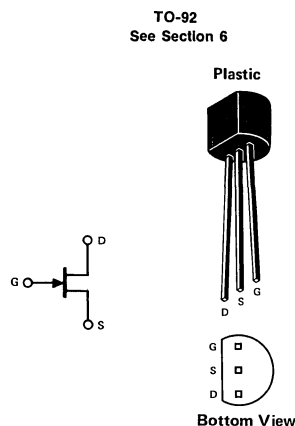
- **General Purpose Amplifiers**
- **Analog Switches**

BENEFITS

- Low Cost
- Automatic Insertion Package

ABSOLUTE MAXIMUM RATINGS (25°C)

Drain-Gate Voltage	20V
Source-Gate Voltage	20V
Drain-Source Voltage	20V
Forward Gate Current	10 mA
Total Device Dissipation at 25°C Ambient (Derate 3.27 mW/°C)	360 mW
Operating Temperature Range	-55 to 135°C
Storage Temperature Range	-55 to 150°C
Lead Temperature Range (1/16" from case for 10 seconds)	300°C



ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic				Min	Typ	Max	Unit	Test Conditions	
1	S T A T I C	I _{GSS}	Gate-Reverse Current		−.01	−100	nA	V _{GS} = −10 V, V _{DS} = 0	
2		BV _{GSS}	Gate-Source Breakdown Voltage	−20			V	I _G = −10 μA, V _{DS} = 0	
3		V _{GS(off)}	Gate-Source Cutoff Voltage	−0.5		−10.0		V _{DS} = 10 V, I _D = 1 μA	
4		I _{DSS}	Saturation Drain Current	0.5		20	mA	V _{DS} = 10 V, V _{GS} = 0 (Note 1)	
5	D Y N A M I C	g _{fs}	Common-Source Forward Transconductance	500			μmho	V _{DS} = 10 V, V _{GS} = 0	f = 1 kHz
6		g _{os}	Common-Source Output Conductance		10				
7		C _{iss}	Common-Source Input Capacitance		4.5				
8		C _{rss}	Common-Source Reverse Transfer Capacitance		1.0		pF		f = 1 MHz

NRL/NPA/NH

NOTE:

1. Pulse test PW $\leq$ 630 msec, duty cycle $\leq$ 10%.